

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSIV)

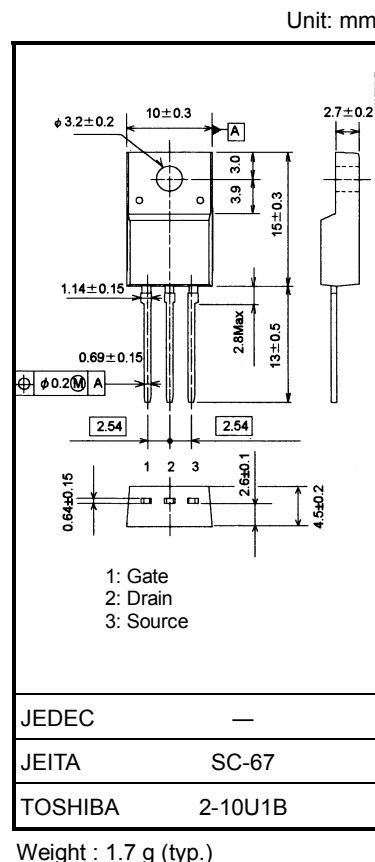
2SK3798

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 2.5\ \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 2.8\ S$ (typ.)
- Low leakage current: $I_{DSS} = 100\ \mu A$ ($V_{DS} = 720\ V$)
- Enhancement-mode: $V_{th} = 2.0 \sim 4.0\ V$ ($V_{DS} = 10\ V$, $I_D = 1\ mA$)

Maximum Ratings ($T_a = 25^\circ C$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	900	V
Drain-gate voltage ($R_{GS} = 20\ k\Omega$)	V_{DGR}	900	V
Gate-source voltage	V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	A
	Pulse ($t = 1\ ms$) (Note 1)	I_{DP}	
Drain power dissipation ($T_c = 25^\circ C$)	P_D	40	W
Single pulse avalanche energy (Note 2)	E_{AS}	345	mJ
Avalanche current	I_{AR}	4	A
Repetitive avalanche energy (Note 3)	E_{AR}	4.0	mJ
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature range	T_{stg}	$-55 \sim 150$	$^\circ C$



Weight : 1.7 g (typ.)

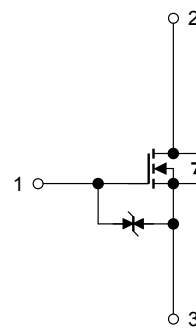
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	3.125	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

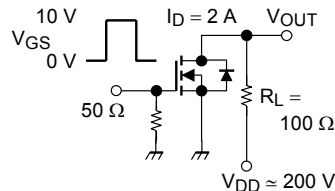
Note 1: Please use devices on conditions that the channel temperature is below $150^\circ C$.Note 2: $V_{DD} = 90\ V$, $T_{ch} = 25^\circ C$, $L = 39.6\ mH$, $I_{AR} = 4.0\ A$, $R_G = 25\ \Omega$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



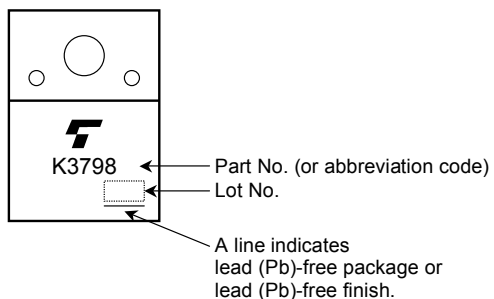
Electrical Characteristics (Ta = 25°C)

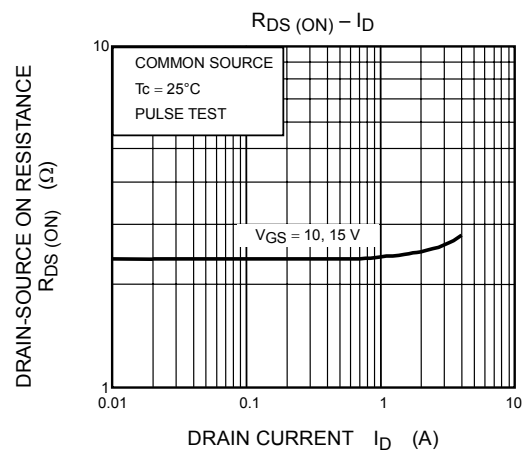
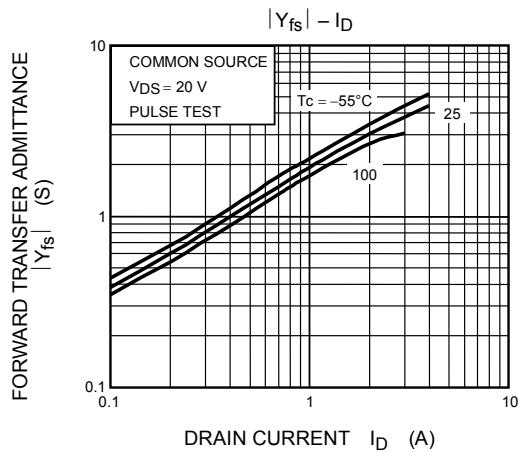
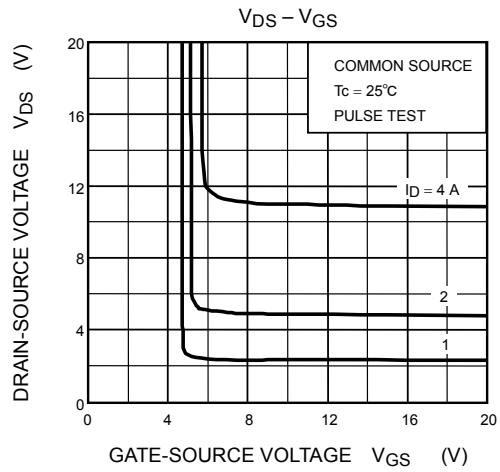
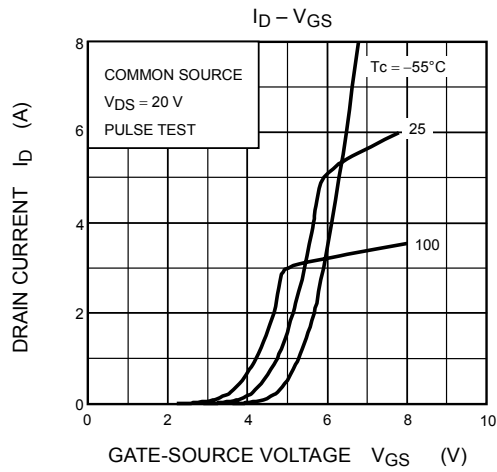
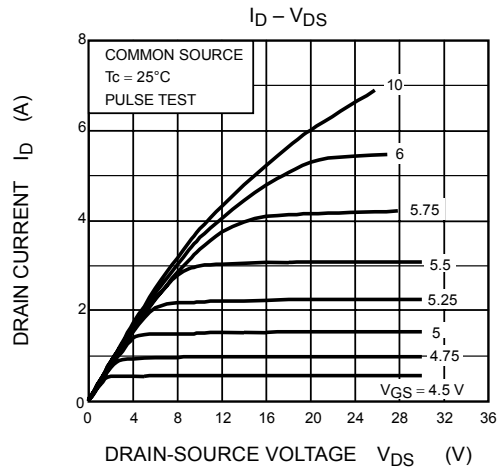
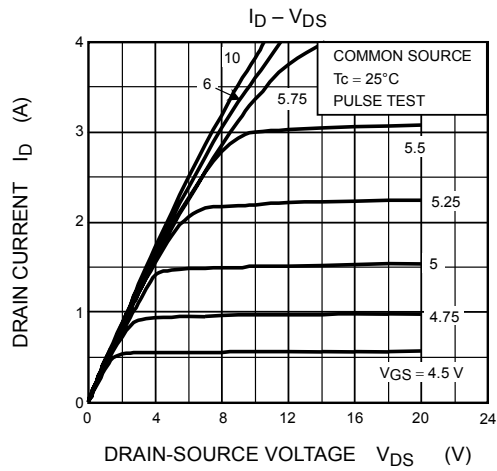
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V
Drain cut-off current		I_{DSS}	$V_{DS} = 720 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	900	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$	—	2.5	3.5	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 20 \text{ V}, I_D = 2 \text{ A}$	1.4	2.8	—	S
Input capacitance		C_{iss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	800	—	pF
Reverse transfer capacitance		C_{rss}		—	20	—	
Output capacitance		C_{oss}		—	85	—	
Switching time	Rise time	t_r		—	20	—	ns
	Turn-on time	t_{on}		—	65	—	
	Fall time	t_f		—	45	—	
	Turn-off time	t_{off}		—	165	—	
Total gate charge		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$	—	26	—	nC
Gate-source charge		Q_{gs}		—	14	—	
Gate-drain charge		Q_{gd}		—	12	—	

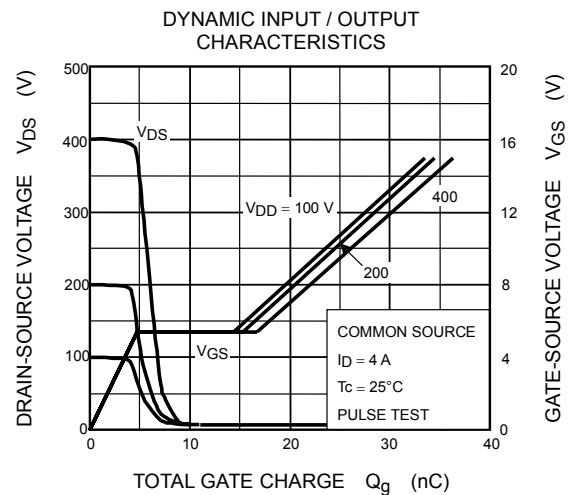
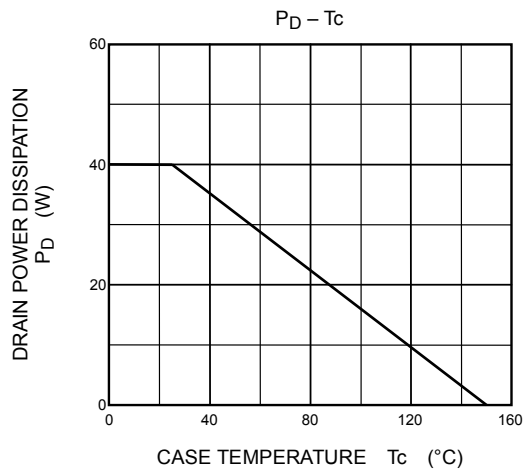
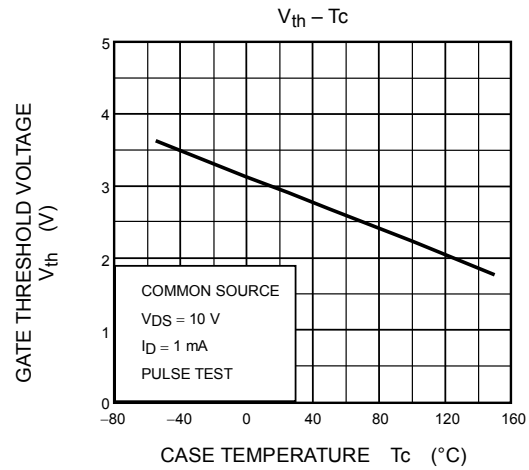
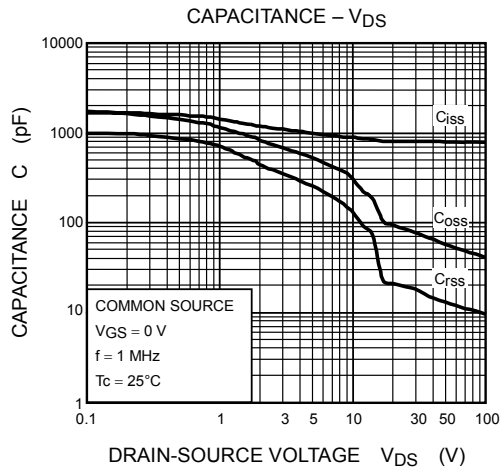
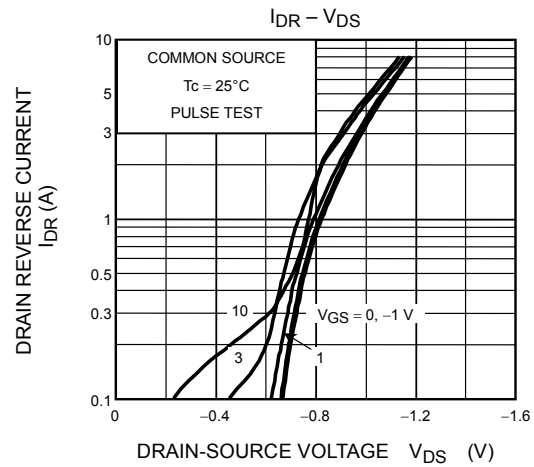
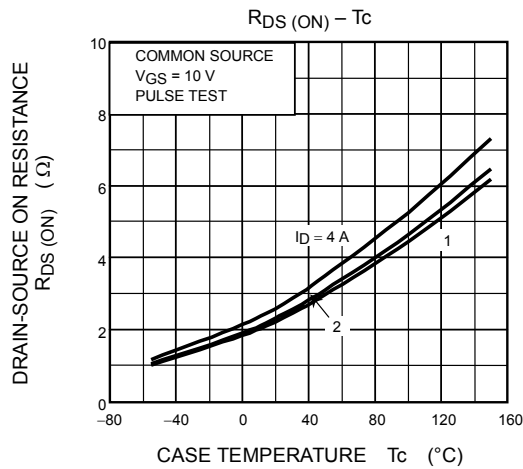
Source-Drain Ratings and Characteristics (Ta = 25°C)

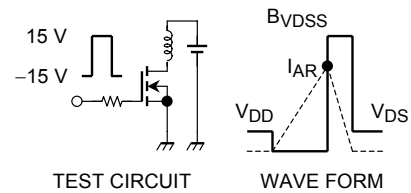
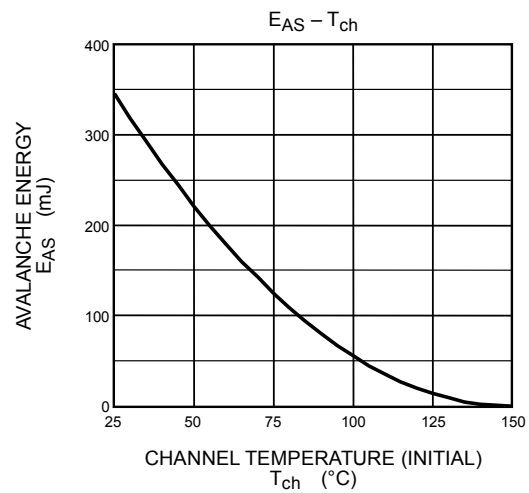
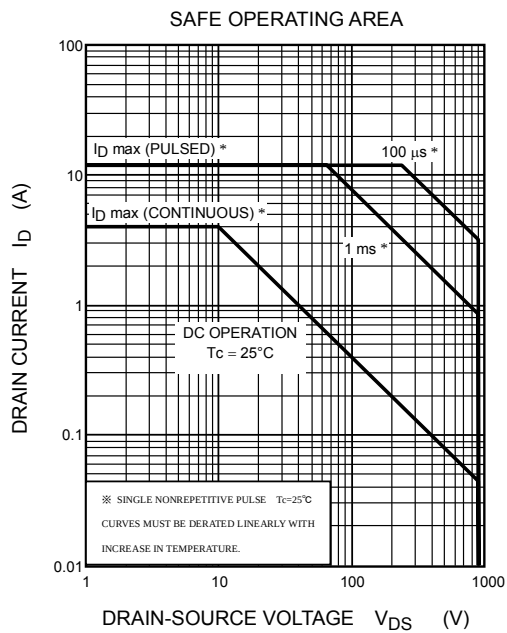
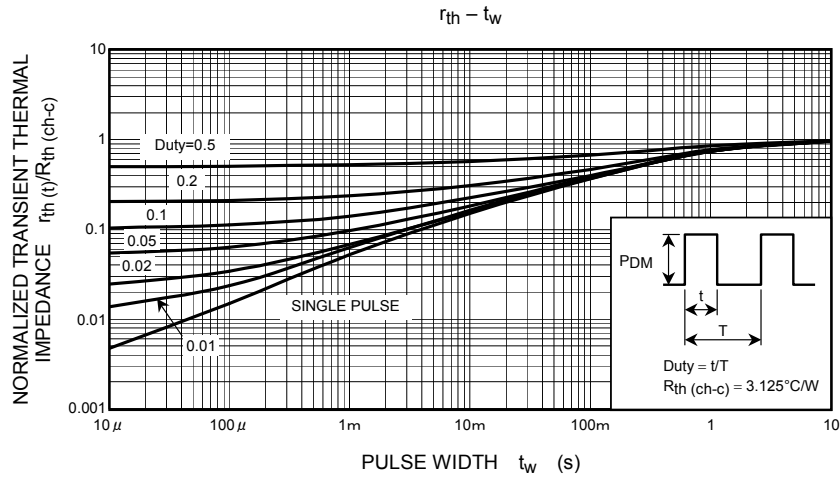
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	4	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	12	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 4 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 4 \text{ A}, V_{GS} = 0 \text{ V},$ $dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	1100	—	ns
Reverse recovery charge	Q_{rr}		—	8.3	—	μC

Marking









$$R_G = 25 \, \Omega$$

$$V_{DD} = 90 \, V, L = 39.6 \, mH$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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